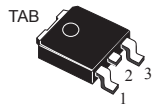
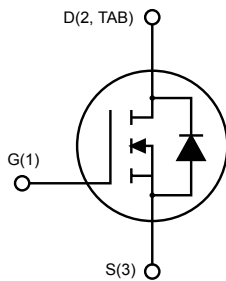


Automotive-grade N-channel 55 V, 6.5 mΩ typ., 80 A STripFET F3 Power MOSFET in a DPAK package



DPAK




AM01475v1_noZen



Features

Type	V _{DS}	R _{DS(on)} max.	I _D	P _{TOT}
STD65N55F3	55 V	8.5 mΩ	80 A	110 W

- AEC-Q101 qualified 
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using STripFET™ F3 technology. It is designed to minimize on-resistance and gate charge to provide superior switching performance.

Product status

STD65N55F3

Product summary

Order code	STD65N55F3
Marking	65N55F3
Package	DPAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	55	V
V_{GS}	Gate-source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	80	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	56	A
$I_{DM}^{(1)}$	Drain current (pulsed)	320	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
$dv/dt^{(2)}$	Peak diode recovery	11	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	390	mJ
T_j	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
T_{stg}	Storage temperature range		

1. Pulse width is limited by safe operating area.
2. $I_{SD} \leq 65\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{jmax}$
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 32\text{ A}$, $V_{DD} = 25\text{ V}$

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.36	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	50	$^\circ\text{C}/\text{W}$

1. When mounted on an 1- inch² FR-4 board, 2oz Cu.

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }\mu\text{A}$	55			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 55\text{ V}$			10	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 55\text{ V}$, $T_C = 125\text{ °C}^{(1)}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0\text{ V}$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	2		4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 32\text{ A}$		6.5	8.5	m Ω

1. Defined by design, not subject to production test.

Table 4. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	2200		pF
C_{oss}	Output capacitance		-	500		pF
C_{riss}	Reverse transfer capacitance		-	25		pF
Q_g	Total gate charge	$V_{DD} = 27\text{ V}$, $I_D = 65\text{ A}$,	-	33.5	45	nC
Q_{gs}	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	12.5		nC
Q_{gd}	Gate-drain charge	(see Figure 13. Test circuit for gate charge behavior)	-	9.5		nC

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 27\text{ V}$, $I_D = 32\text{ A}$,	-	20	-	ns
t_r	Rise time	$R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	50	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	35	-	ns
t_f	Fall time		-	11.5	-	ns

Table 6. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				320	A
V_{SD}	Forward on voltage	$I_{SD} = 65 \text{ A}, V_{GS} = 0 \text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 65 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s},$ $V_{DD} = 25 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times)	-	47		ns
Q_{rr}	Reverse recovery charge		-	87		nC
I_{RRM}	Reverse recovery current		-	3.7		A

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

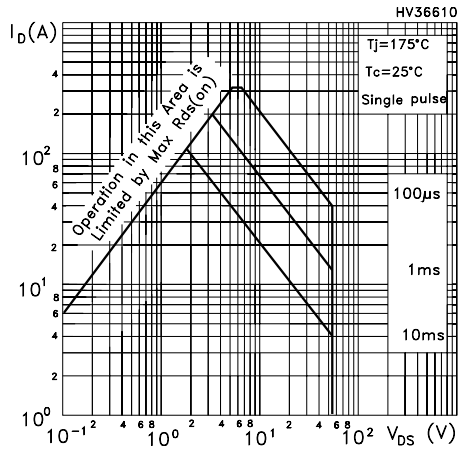


Figure 2. Thermal impedance

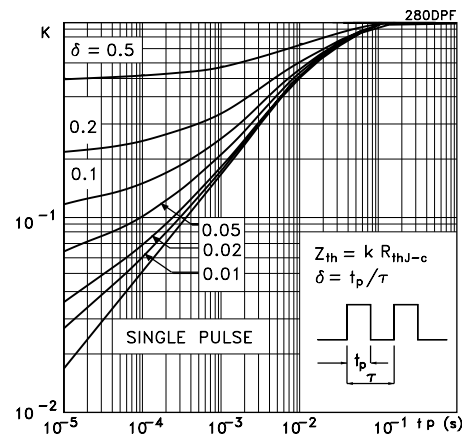


Figure 3. Output characteristics

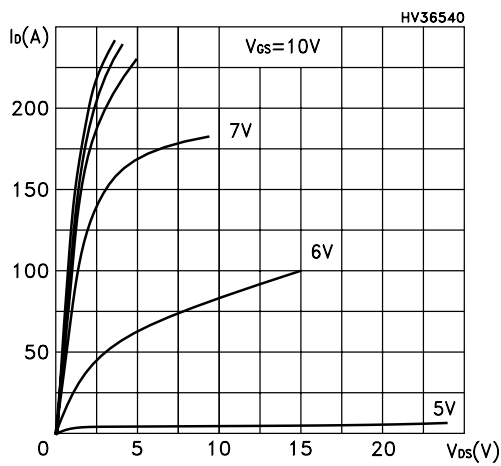


Figure 4. Transfer characteristics

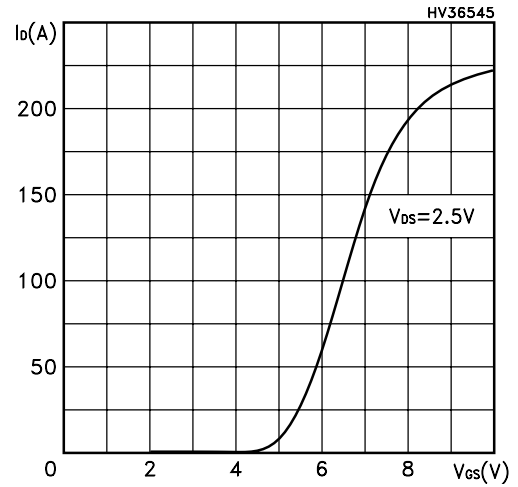


Figure 5. Normalized $V_{(BR)DSS}$ vs temperature

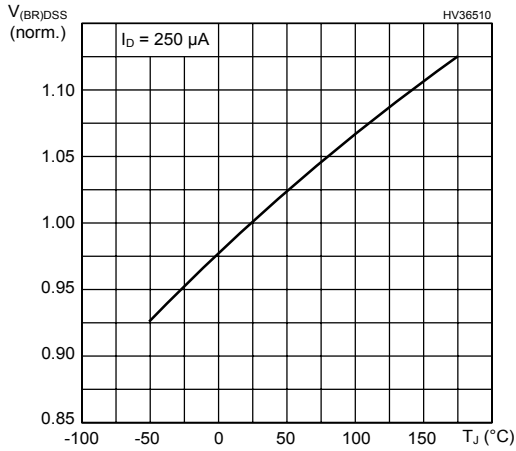


Figure 6. Static drain-source on-resistance

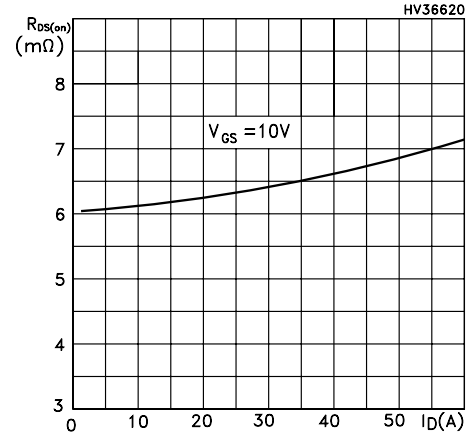


Figure 7. Gate charge vs gate-source voltage

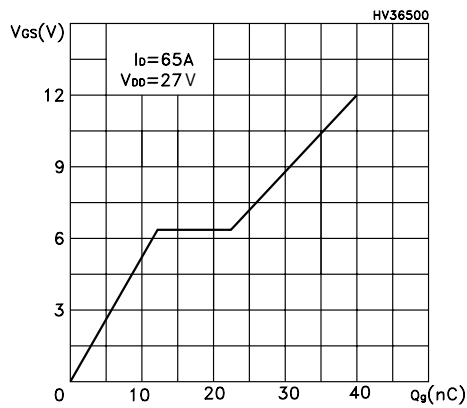


Figure 8. Capacitance variations

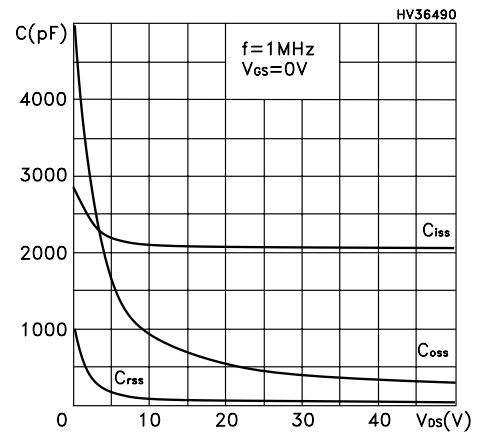


Figure 9. Normalized gate threshold voltage vs temperature

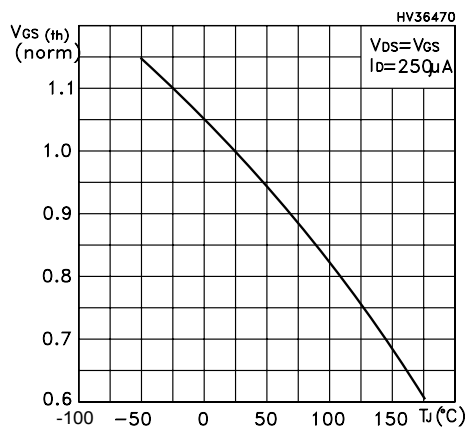


Figure 10. Normalized on-resistance vs temperature

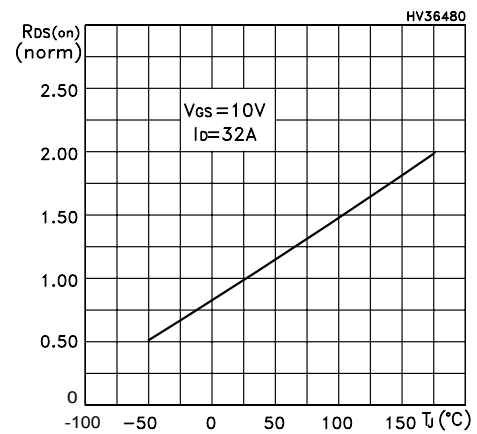
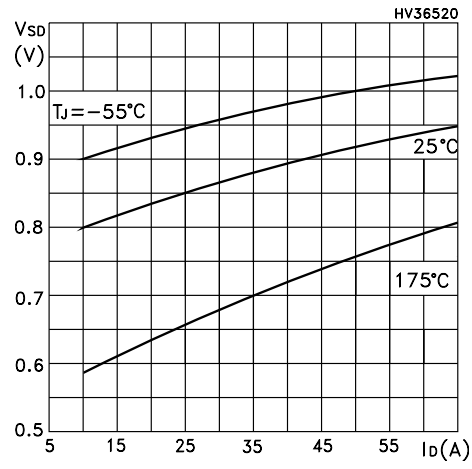


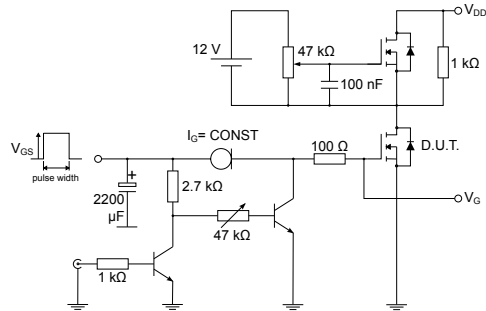
Figure 11. Source-drain diode forward characteristics



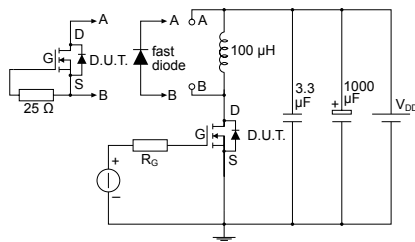
3 Test circuits

Figure 12. Test circuit for resistive load switching times

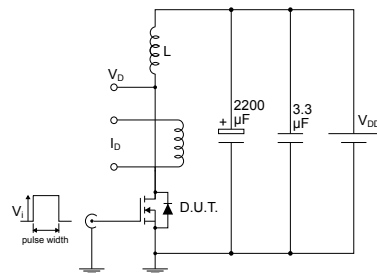

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Figure 13. Test circuit for gate charge behavior


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Figure 14. Test circuit for inductive load switching and diode recovery times


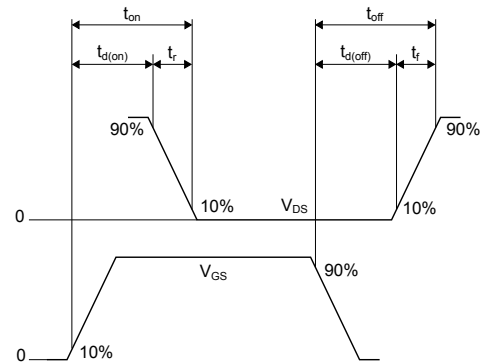
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Figure 15. Unclamped inductive load test circuit


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Figure 16. Unclamped inductive waveform


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Figure 17. Switching time waveform


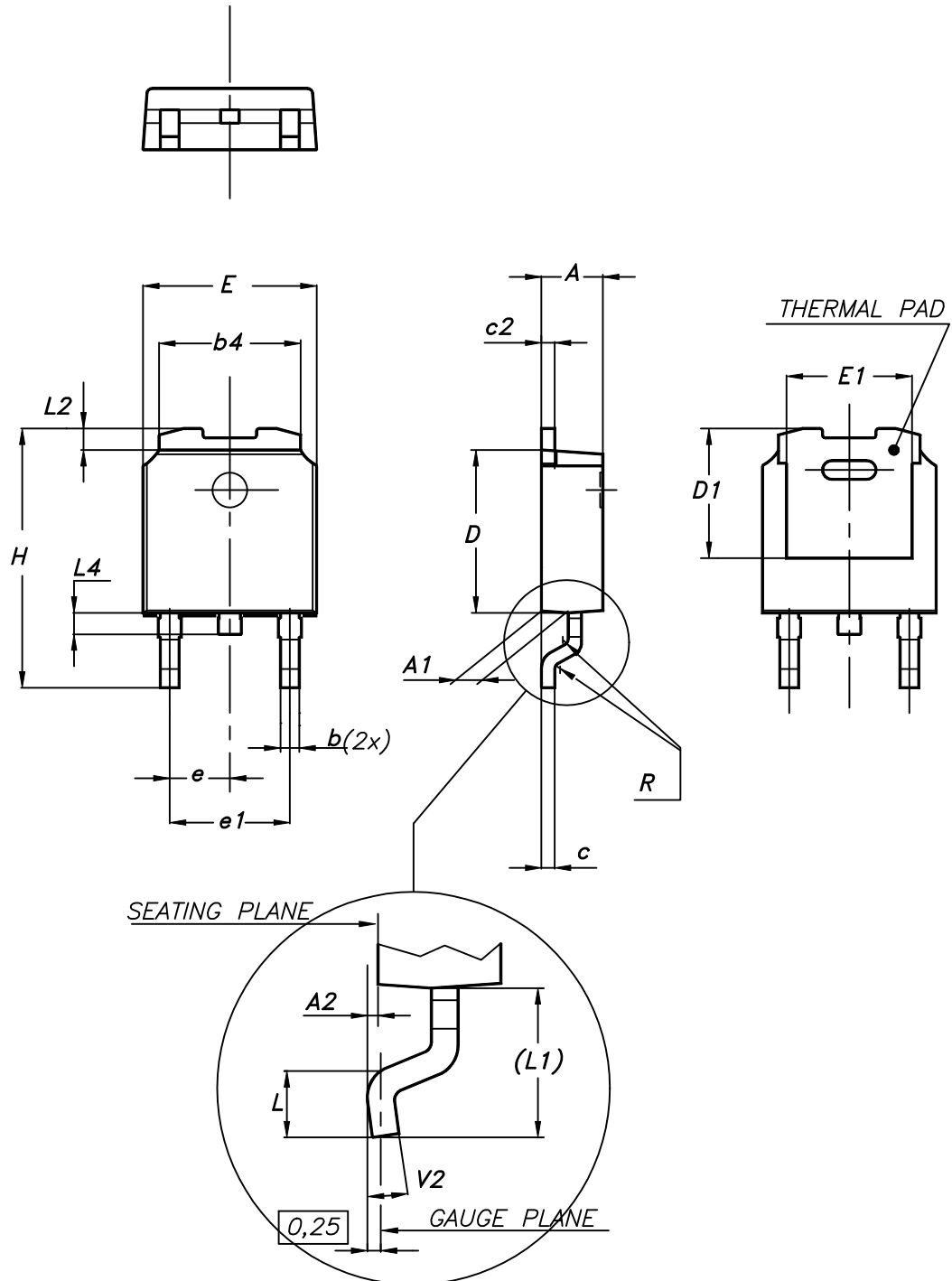
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 DPAK (TO-252) type A2 package information

Figure 18. DPAK (TO-252) type A2 package outline

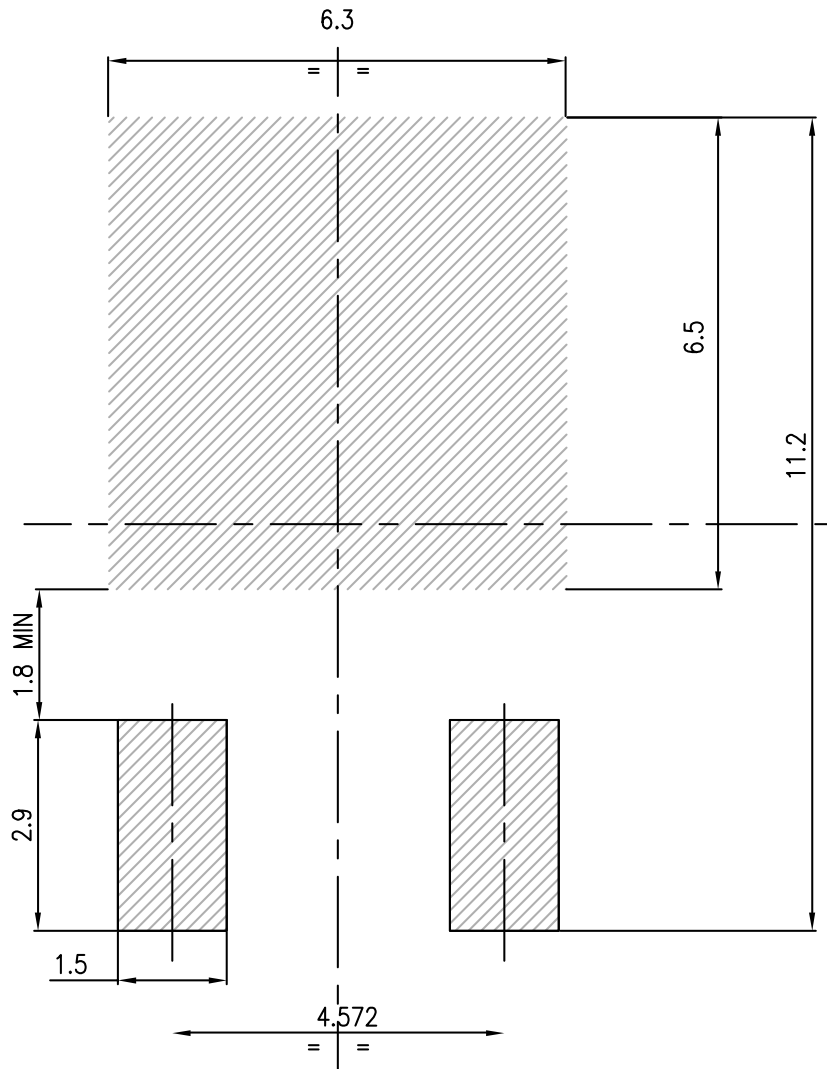


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Table 7. DPAK (TO-252) type A2 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1	4.95	5.10	5.25
E	6.40		6.60
E1	5.10	5.20	5.30
e	2.159	2.286	2.413
e1	4.445	4.572	4.699
H	9.35		10.10
L	1.00		1.50
L1	2.60	2.80	3.00
L2	0.65	0.80	0.95
L4	0.60		1.00
R		0.20	
V2	0°		8°

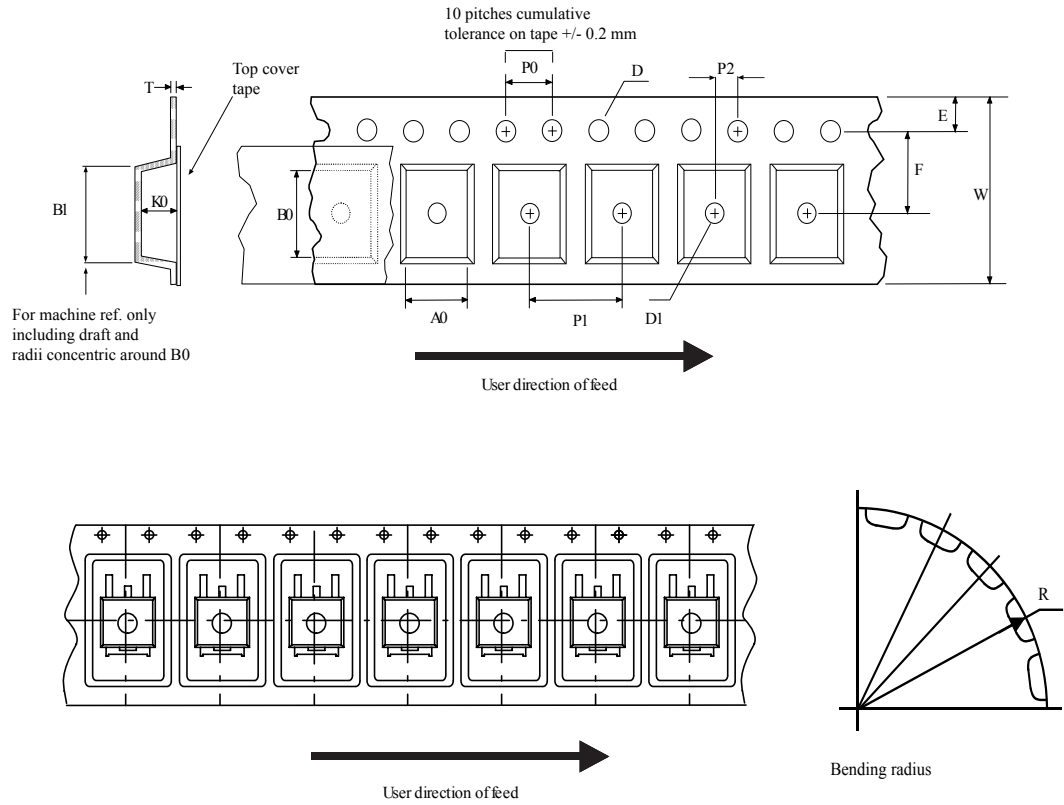
Figure 19. DPAK (TO-252) recommended footprint (dimensions are in mm)



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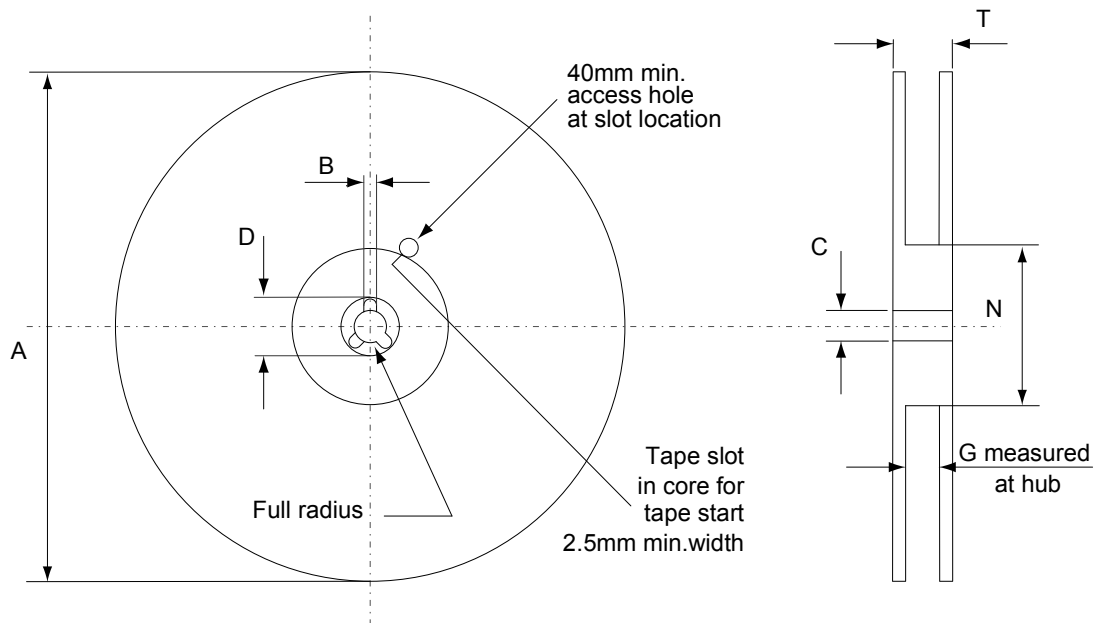
4.2 DPAK (TO-252) packing information

Figure 20. DPAK (TO-252) tape outline



AM08852v1

Figure 21. DPAK (TO-252) reel outline



AM06038v1

Table 8. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1		Base qty.	2500
P1	7.9	8.1		Bulk qty.	2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

Revision history

Table 9. Document revision history

Date	Version	Changes
08-Feb-2007	1	First release.
22-Feb-2007	2	Description has been changed
11-May-2007	3	Improved current values
13-Feb-2018	4	Updated information on cover page. Updated Section 1 Electrical ratings and Section 2 Electrical characteristics . Updated Section 4.1 DPAK (TO-252) type A2 package information . Minor text changes.
17-Jan-2019	5	Updated Section 4.1 DPAK (TO-252) type A2 package information . Minor text changes.

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